

regions 207a and 207b and drain regions 208a and 208b each comprises a p-type impurity region having a fourth concentration. This is shown in Fig. 3C. It is clear from the application that the p-type immunity region is not a LDD region but is a heavy doped region according to a counter doping process. See e.g. page 25, ln. 4 - page 26, ln. 3 of the present application and Figs. 2C-2D. Hence, the objected to limitation is clearly supported by the specification and drawings.

Accordingly, it is respectfully submitted that this objection is in error and it is requested that it now be withdrawn.

II. Claim Rejections - 35 USC §112

The Examiner also rejects Claims 1, 3, 21, 23, 25, 27 and 53 under 35 USC §112, first paragraph, as allegedly containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. This rejection is respectfully traversed.

More specifically, the Examiner states that it is not clear where in the originally filed specification support for “wherein the p-channel TFT of the driver circuit does not have a LDD region” can be found. However, the specification clearly supports this limitation, as explained above. In particular, page 29, lns. 12 - 15 and page 29, ln. 24 - page 30, ln. 3 of the present application state that p-channel TFT 200, source regions 207a and 207b and drain regions 208a and 208b each comprises a p-type impurity region having a fourth concentration. See also Fig. 3C. It is clear from the application that the p-type immunity region is not a LDD region but is a heavy doped region according to a counter doping process. See e.g. page 25, ln. 4 - page 26, ln. 3 of the present application and Figs. 2C-2D. Hence, this clearly shows regions of the p-channel TFT of the

driver circuit which do not have LDD. Therefore, the objected to language supported by the specification as originally filed.

Accordingly, it is respectfully requested that this rejection now be withdrawn.

III. Claim Rejections - 35 USC §103

In the Office Action, the Examiner has the following rejections under 35 USC §103:

- a. Claims 1 and 25 as being unpatentable over Matsumoto in view of Shimone and Adan et al.;
- b. Claims 3 and 27 as being unpatentable over Matsumoto in view of Shimone, Karauchi et al. and Adan et al.;
- c. Claims 21 and 23 as being unpatentable over Matsumoto in view of Shimone, Karauchi et al. and Adan et al. and further in view of Hioki; and
- d. Claim 53 as being unpatentable over Matsumoto in view of Shimone, Takasu and Adan.

Each of these rejections is respectfully traversed.

The present invention, as recited in the amended independent claims, is directed in general to a semiconductor device comprising:

- a pixel TFT disposed in a pixel section over a substrate; and
- a driver circuit comprising a p-channel TFT and an n-channel TFT, over the substrate;
- a first interlayer insulating film comprising an inorganic insulating material over a gate electrode of the pixel TFT;
- a second interlayer insulating film comprising an organic insulating material over the first interlayer insulating film; and

a pixel electrode having a light reflective surface over the second interlayer insulating film, and electrically connected with the pixel TFT through an opening in the first and second interlayer insulating films,

wherein the p-channel TFT of the driver circuit comprises a channel forming region, a source region and a drain region in contact with the channel forming region,

wherein the p-channel TFT of the driver circuit does not have a LDD region,

wherein the n-channel TFT of the driver circuit comprises a channel forming region, an n-type impurity region of a first concentration which forms at least one LDD region in contact with the channel forming region and partly overlapping the gate electrode, and a source region and a drain region in contact with the at least one LDD region,

wherein the pixel TFT comprises a channel forming region, at least one LDD region in contact with the channel forming region, and a source region and a drain region in contact with the at least one LDD region.

In contrast to the Examiner's contention, it appears that Matsumoto discloses each of the pixel TFT, the p-channel TFT, and the n-channel TFT having a pair of LDD regions. Hence, it does not have a p-channel TFT of the driver circuit which does not have a LDD region. As this feature does not appear to be disclosed or suggested by the other cited references, the claims of the present application are not disclosed or suggested by the cited references and are patentable thereover.

Accordingly, it is respectfully requested that the rejections of the claims be withdrawn, and the claims allowed.

IDS

The undersigned is preparing an IDS. One of the references, however, is not due to issue

until tomorrow. As soon as the undersigned gets a copy of this reference, an IDS will be submitted. It is requested that this IDS be considered and that no further action be issued until this IDS has been considered.

Conclusion

It is respectfully submitted that the present application is now in a condition for allowance and should be allowed.

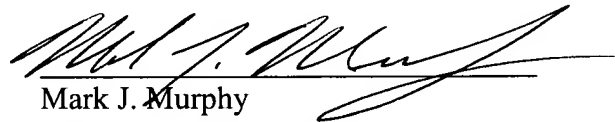
Please charge our deposit account 50/1039 for any further fee for this amendment.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

Date:

June 9, 2003


Mark J. Murphy
Registration No. 34,225

COOK, ALEX, McFARRON, MANZO,
CUMMINGS & MEHLER, LTD.
200 West Adams Street; Suite 2850
Chicago, Illinois 60606
(312) 236-8500